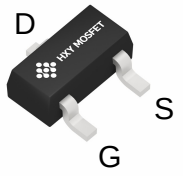
Description

The RRR030P03 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



SOT-23-3L
(SOT-346)

General Features

V_{DS} = -30V I_D =-4.2A

$R_{DS(ON)}$ < 54mΩ@ V_{GS}=10V

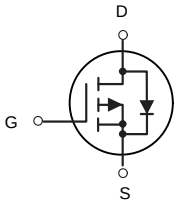
$R_{DS(ON)}$ < 77mΩ@ V_{GS}=4.5V

Application

Battery protection

Load switch

Uninterruptible power supply



P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
RRR030P03	SOT-23-3L(SOT-346)	HXY MOSFET	3000

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	±12	V
I_D	Drain Current-Continuous	-4.2	A
I_{DM}	Drain Current-Pulsed (Note 1)	-30	A
P_D	Maximum Power Dissipation	1.2	W
T_J,T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	℃
$R_{\theta JA}$	Thermal Resistance,Junction-to-Ambient (Note 2)	104	℃/W

Electrical Characteristics (T_A=25℃unless otherwise noted)

Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-24V,V_{GS}=0V	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±10V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	-0.7	-1	-1.3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-4.2A	-	46	54	mΩ
		V_{GS}=-4.5V, I_D=-4A	-	58	77	mΩ
		V_{GS}=-2.5V, I_D=-1A		74	130	mΩ
Forward Transconductance	g_{FS}	V_{DS}=-5V,I_D=-4.2A	-	10	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=-15V,V_{GS}=0V, F=1.0MHz	-	880	-	PF
Output Capacitance	C_{oss}		-	105	-	PF
Reverse Transfer Capacitance	C_{rss}		-	65	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-15V,I_D=-4.2A V_{GS}=-10V,R_{GEN}=6Ω	-	7	-	nS
Turn-on Rise Time	t_r		-	3	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	30	-	nS
Turn-Off Fall Time	t_f		-	12	-	nS
Total Gate Charge	Q_g	V_{DS}=-15V,I_D=-4.2A,V_{GS}=-4.5V	-	8.5	-	nC
Gate-Source Charge	Q_{gs}		-	1.8	-	nC
Gate-Drain Charge	Q_{gd}		-	2.7	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=-4.2A	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

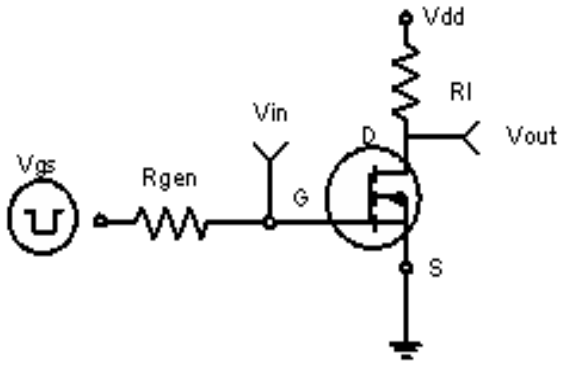


Figure 1:Switching Test Circuit

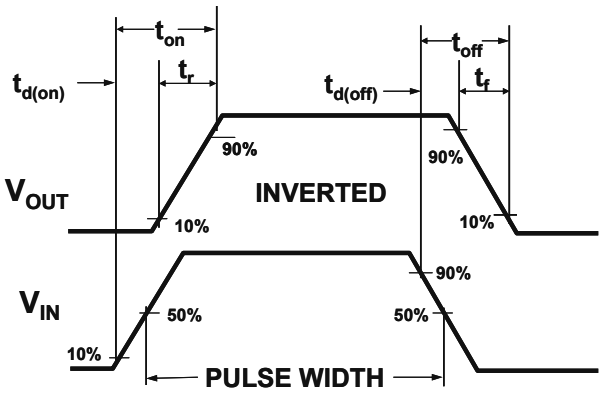
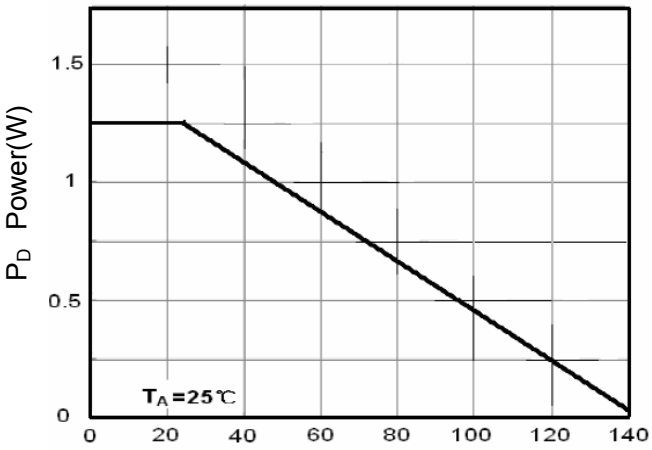
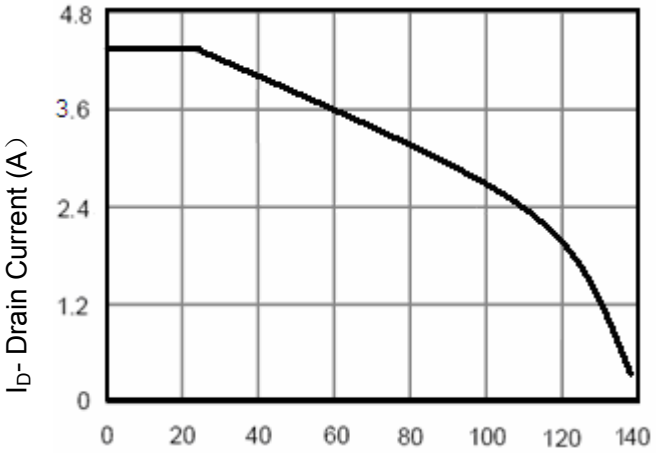


Figure 2:Switching Waveforms



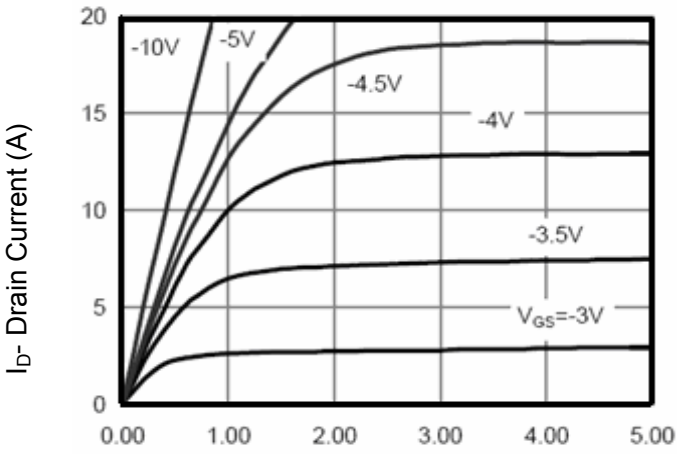
T_J-Junction Temperature(℃)

Figure 3 Power Dissipation



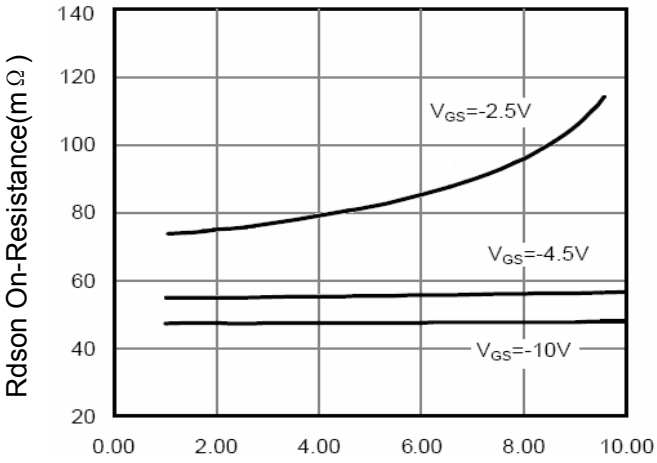
T_J-Junction Temperature(℃)

Figure 4 Drain Current



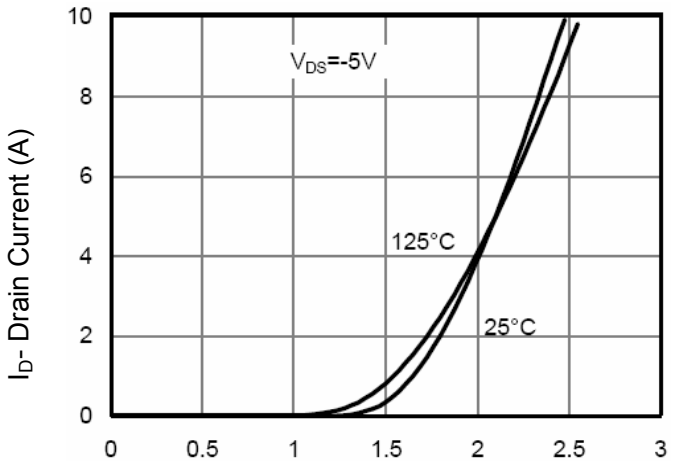
Vds Drain-Source Voltage (V)

Figure 5 Output Characteristics



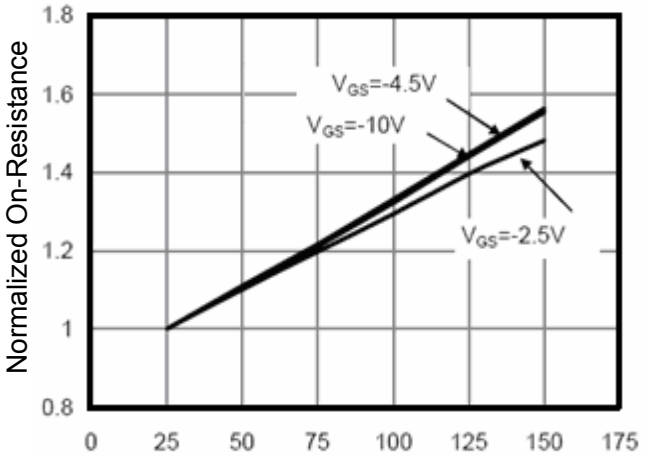
I_D- Drain Current (A)

Figure 6 Drain-Source On-Resistance



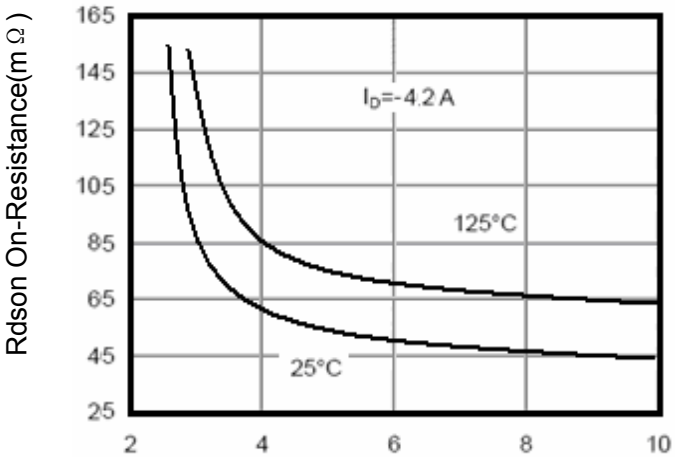
Vgs Gate-Source Voltage (V)

Figure 7 Transfer Characteristics



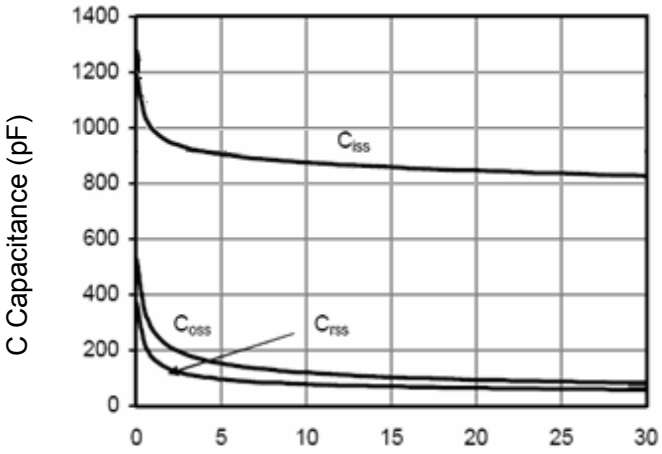
T_J-Junction Temperature(℃)

Figure 8 Drain-Source On-Resistance



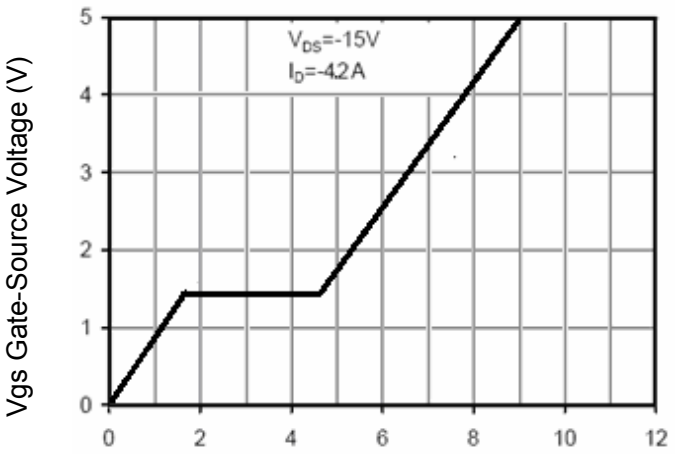
Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs



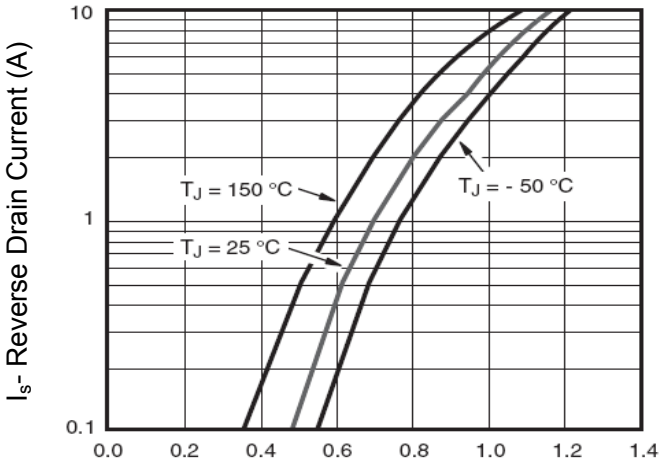
Vds Drain-Source Voltage (V)

Figure 10 Capacitance vs Vds



Qg Gate Charge (nC)

Figure 11 Gate Charge



Vsd Source-Drain Voltage (V)

Figure 12 Source- Drain Diode Forward

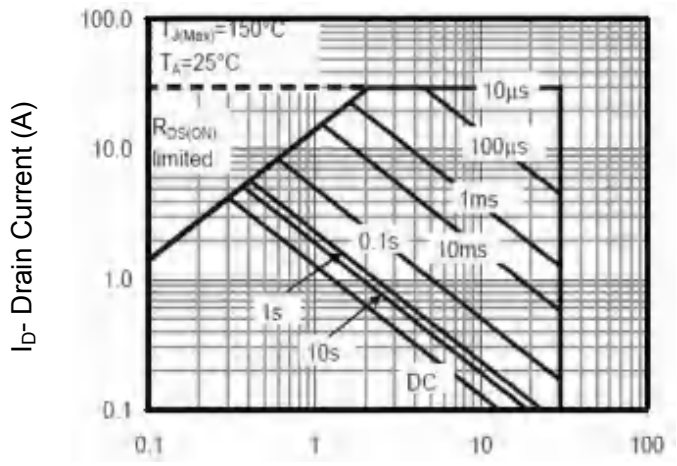


Figure 13 Safe Operation Area

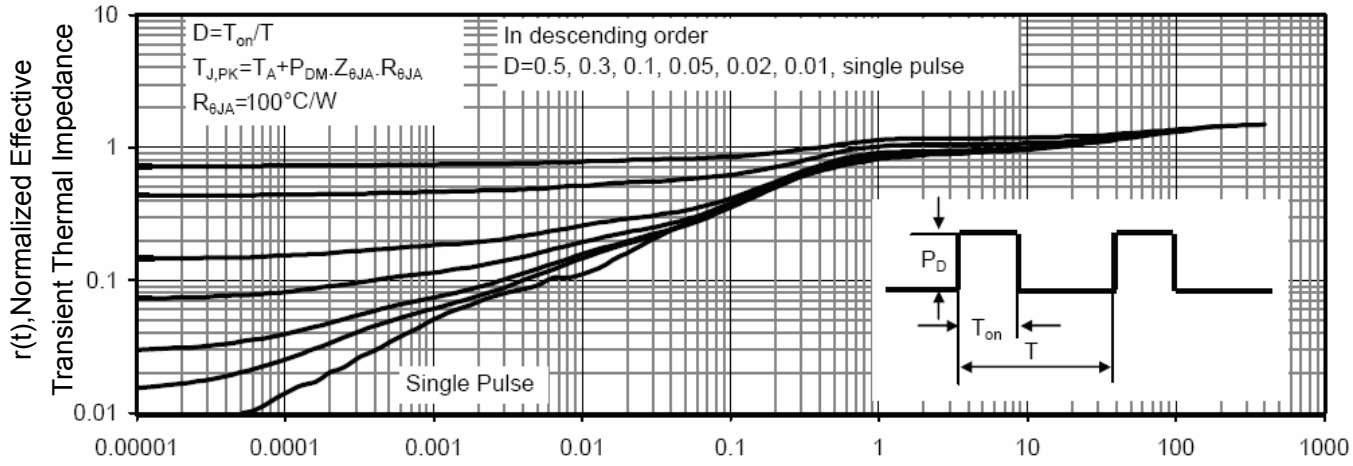
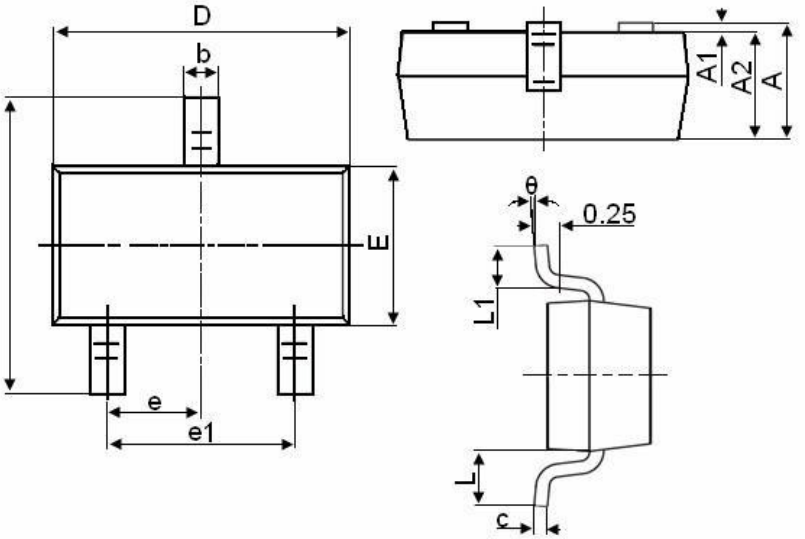


Figure 14 Normalized Maximum Transient Thermal Impedance

SOT-23-3L(SOT-346) Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.800	3.000
E	1.500	1.700
E1	2.650	2.950
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.600
θ	0°	8°

Attention

■ Any and all HUA XUAN YANG ELECTRONICS products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your HUA XUAN YANG ELECTRONICS representative nearest you before using any HUA XUAN YANG ELECTRONICS products described or contained herein in such applications.

■ HUA XUAN YANG ELECTRONICS assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein.

■ Specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

■ HUA XUAN YANG ELECTRONICS CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could
give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

■ In the event that any or all HUA XUAN YANG ELECTRONICS products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

■ No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of HUA XUAN YANG ELECTRONICS CO.,LTD.

■ Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. HUA XUAN YANG ELECTRONICS believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

■ Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the HUA XUAN YANG ELECTRONICS product that you intend to use.

Unikeyic Electronics

Global Electronic Components Distributor

Click to view pricing, inventory, delivery, and lifecycle information:

HXY MOSFET:

HXY8205ES US2M P6SMB36CA SS510C SS1045 BZT52C3V3S DTC143ZE HAD8542ARZ HXY2101EI SS10100 BZT52C13 HMCP602-I/SN HOPA2340UA IRLML6246PBF SD15C SQJA04EP-T1_BE3 MAX487ESA P6SMB33CA PESD5V0S1BB SS5150B HC4D20120A HT7150 P6SMB200A TPSMB100CA-VR TPSMB28A-VR HESDNC5VB1AF-B HT7540-1 HXY2300MI MMBT3904T HC3D10170A